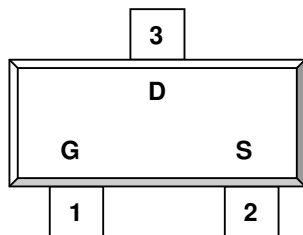
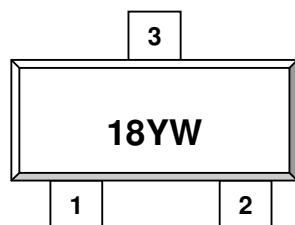


DESCRIPTION

ST2318SRG is the N-Channel logic enhancement mode power field effect transistor is produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management, other battery powered circuits, and low in-line power loss are needed in a very small outline surface mount package.

**PIN CONFIGURATION
SOT-23**


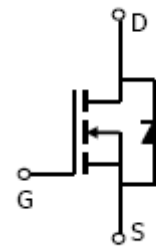
1.Gate 2.Source 3.Drain

**PART MARKING
SOT-23**


Y: Year Code W: Week Code

FEATURE

- 40V/3.9A, $R_{DS(ON)} = 42m\Omega$ (Typ.) @VGS = 10V
- 40V/3.5A, $R_{DS(ON)} = 53m\Omega$ @VGS = 4.5V
- 40V/2.0A, $R_{DS(ON)} = 75 m\Omega$ @VGS = 2.5V
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOT-23 package design



**ST2318SRG**

N Channel Enhancement Mode MOSFET

3.9A

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C Unless otherwise noted)

| Parameter | Symbol | Typical | Unit |
|--|------------------|------------------------------|------|
| Drain-Source Voltage | V _{DSS} | 40 | V |
| Gate-Source Voltage | V _{GSS} | ±20 | V |
| Continuous Drain Current (T _J =150°C) | I _D | T _A =25°C 3.9 | A |
| | | T _A =70°C 3.0 | |
| Pulsed Drain Current | I _{DM} | 10 | A |
| Continuous Source Current (Diode Conduction) | I _S | 1.20 | A |
| Power Dissipation | P _D | T _A =25°C 1.20 | W |
| | | T _A =70°C 0.8 | |
| Operation Junction Temperature | T _J | 150 | °C |
| Storage Temperature Range | T _{STG} | -55/150 | °C |
| Thermal Resistance-Junction to Ambient | R _{θJA} | 100 | °C/W |



ST2318SRG



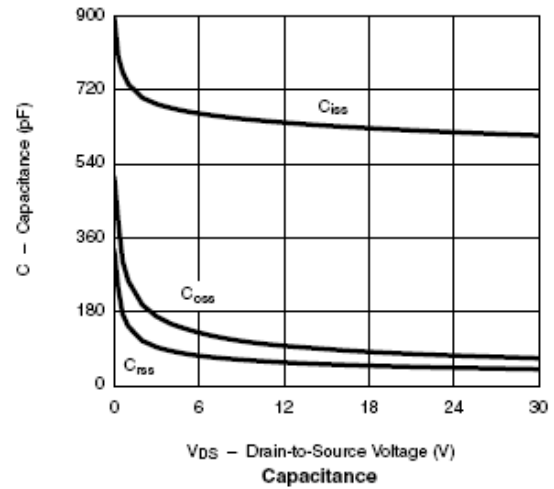
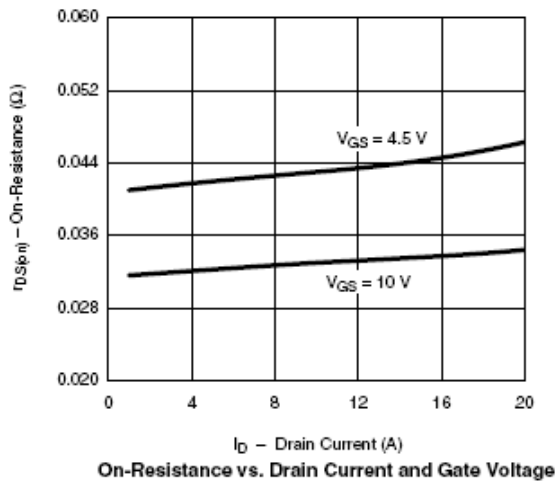
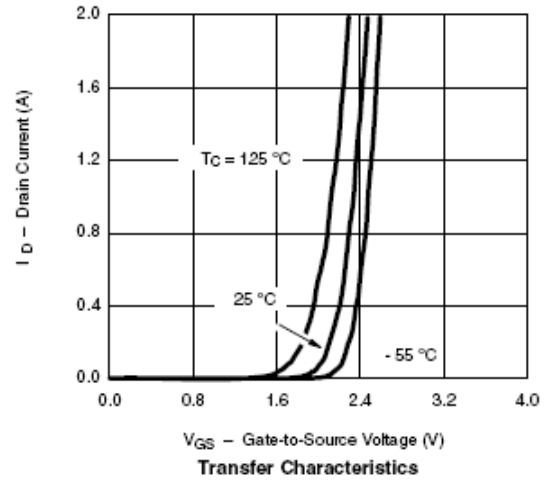
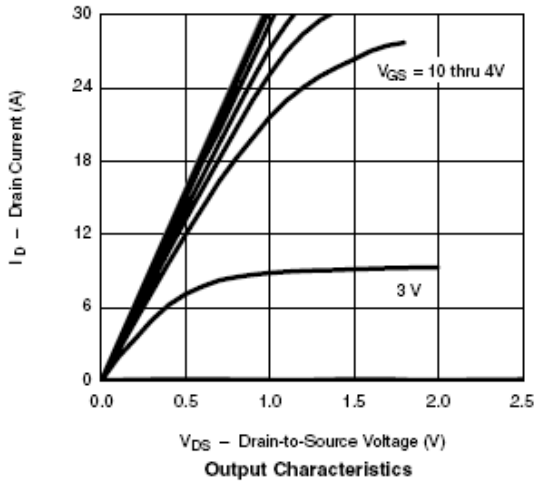
N Channel Enhancement Mode MOSFET

3.9A

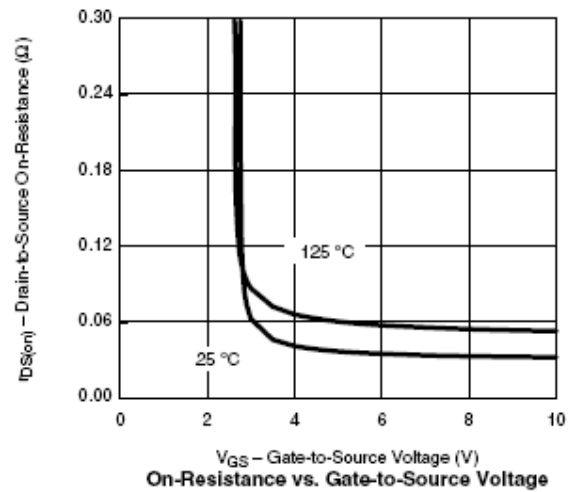
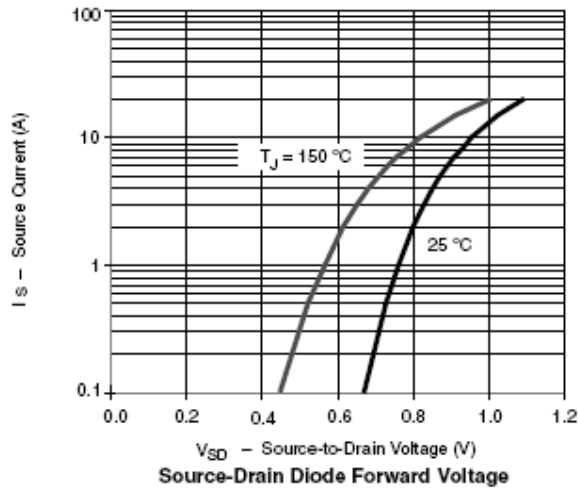
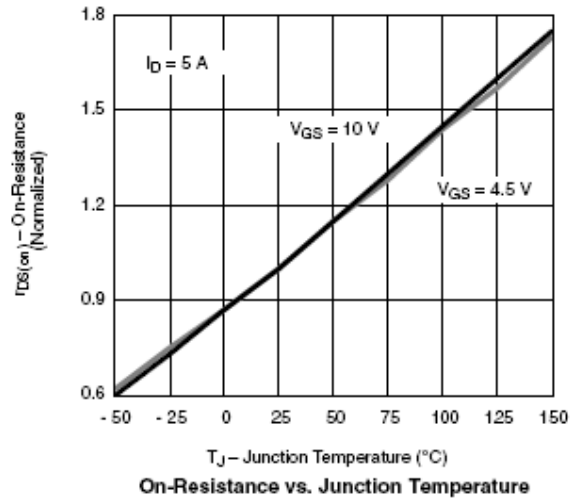
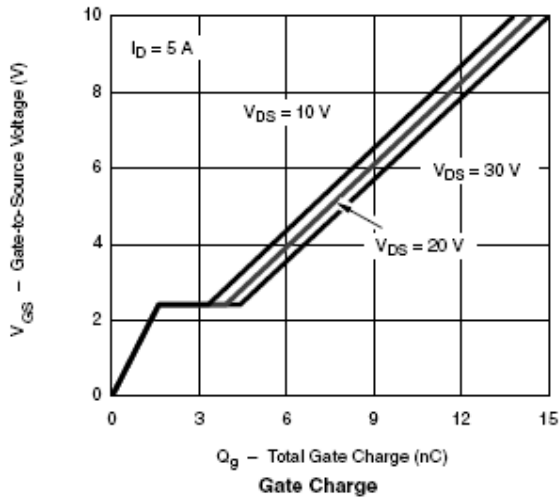
ELECTRICAL CHARACTERISTICS (Ta = 25°C Unless otherwise noted)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|---------------------------------|----------------|--|------|-------------------------|-----------|----------|
| Static | | | | | | |
| Drain-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS}=0V, I_D=250\mu A$ | 40 | | | V |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=250\mu A$ | 0.50 | | 1.2 | V |
| Gate Leakage Current | I_{GSS} | $V_{DS}=0V, V_{GS}=\pm 20V$ | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS}=40V, V_{GS}=0V$ | | | 1 | uA |
| | | $V_{DS}=40V, V_{GS}=0V$ $T_J=85^\circ C$ | | | 5 | |
| Drain-source On-Resistance | $R_{DS(on)}$ | $V_{GS}=10V, I_D=3.9A$ $V_{GS}=4.5V, I_D=3.5A$ $V_{GS}=2.5V, I_D=2.0A$ | | 0.042 0.053 0.075 | | Ω |
| Forward Transconductance | g_{fs} | $V_{DS}=15V, I_D=6.2A$ | | 13 | | S |
| Diode Forward Voltage | V_{SD} | $I_S=2.3A, V_{GS}=0V$ | | 0.8 | 1.2 | V |
| Dynamic | | | | | | |
| Total Gate Charge | Q_g | $V_{DS}=15V$ $V_{GS}=10V$ $I_D=2.0A$ | | 16 | 24 | nC |
| Gate-Source Charge | Q_{gs} | | | 3 | | |
| Gate-Drain Charge | Q_{gd} | | | 2.5 | | |
| Turn-On Time | $t_{d(on)tr}$ | $V_{DD}=15V$ $R_L=15\Omega$ $I_D=1.0A$ $V_{GEN}=10V$ $R_G=6\Omega$ | | 15 | 20 | nS |
| | | | | 6 | 12 | |
| Turn-Off Time | $t_{d(off)tf}$ | | | 10 | 20 | |
| | | | | 40 | 80 | |

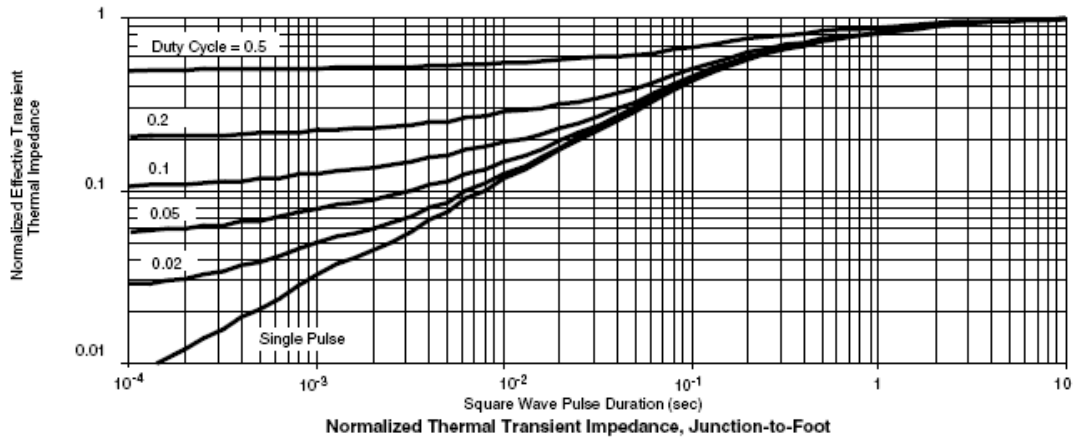
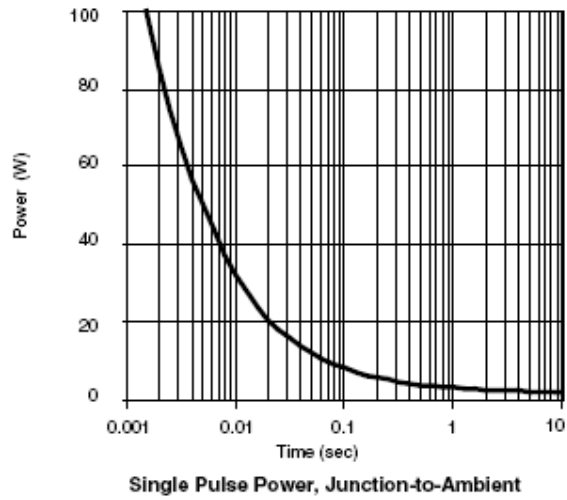
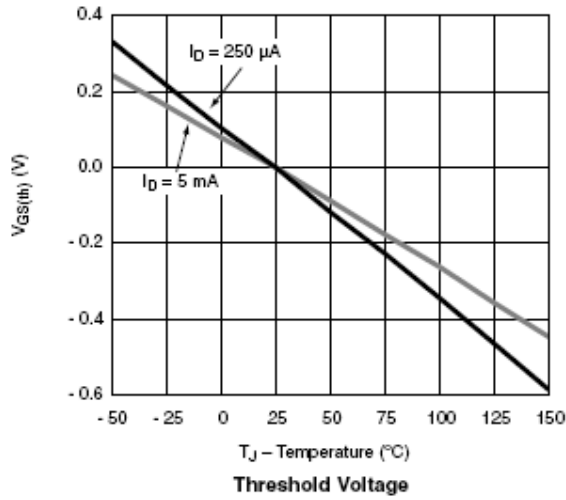
TYPICAL CHARACTERISTICS (25°C Unless noted)

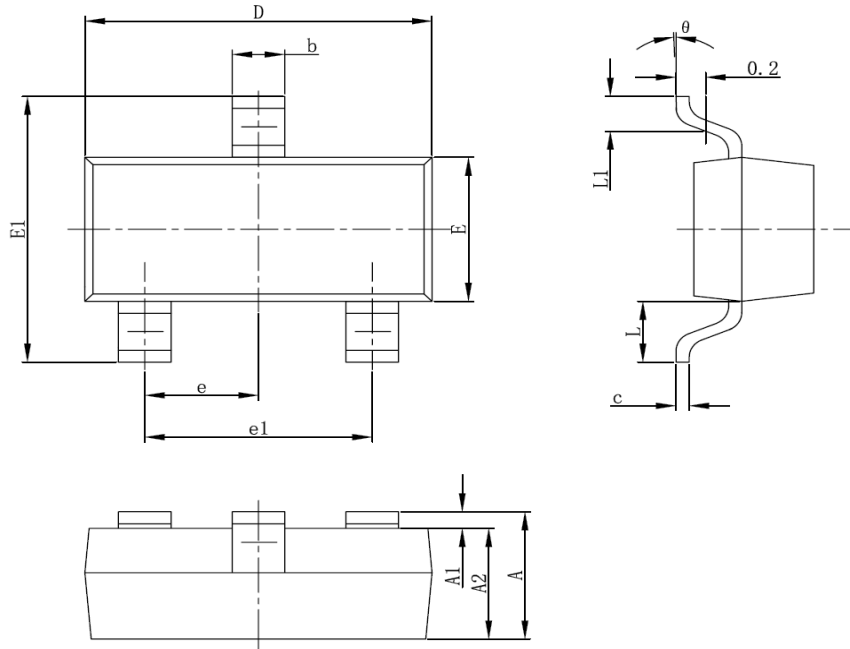


TYPICAL CHARACTERISTICS (25°C Unless noted)



TYPICAL CHARACTERISTICS (25°C Unless noted)



SOT-23 PACKAGE OUTLINE


| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min | Max | Min | Max |
| A | 0.900 | 1.100 | 0.035 | 0.043 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 0.900 | 1.000 | 0.035 | 0.039 |
| b | 0.300 | 0.500 | 0.012 | 0.020 |
| c | 0.080 | 0.150 | 0.003 | 0.006 |
| D | 2.800 | 3.000 | 0.110 | 0.118 |
| E | 1.200 | 1.400 | 0.047 | 0.055 |
| E1 | 2.250 | 2.550 | 0.089 | 0.100 |
| e | 0.950TYP | | 0.037TYP | |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 |
| L | 0.550REF | | 0.022REF | |
| L1 | 0.300 | 0.500 | 0.012 | 0.020 |
| θ | 0° | 8° | 0° | 8° |

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